

**IN THE CLAIMS:**

1. (Currently Amended) A substrate for a micro-fluid ejecting device, the substrate comprising:

a plurality of fluid ejection devices;

a plurality of driver devices for driving the plurality of fluid ejection devices; and

a nonvolatile programmable memory matrix containing embedded programmable memory devices, the matrix ~~being~~ capable of being operatively connected to the micro-fluid ejecting device for storing information for operation of the micro-fluid ejecting device, wherein the memory matrix is erasable by ultraviolet light; and

a layer disposed adjacent the nonvolatile programmable memory matrix, said layer having properties sufficient to block ultraviolet light having a wavelength below about 400 nanometers.

2. (Previously Presented) The substrate of claim 1 wherein the embedded programmable memory devices comprise transistors selected from the group consisting of PMOS and NMOS floating gate transistors.

3. (Previously Presented) The substrate of claim 1 wherein the embedded programmable memory devices have a memory density of greater than about 200 bits per square millimeter.

4. (Previously Presented) The substrate of claim 1 wherein the programmable memory matrix comprises floating gate transistors.

5. (Previously Presented) The substrate of claim 1 wherein the programmable memory matrix comprises more than 128 memory devices.

6. (Previously Presented) The substrate of claim 1 wherein the embedded programmable memory devices are programmable by applying a voltage of greater than about 8 volts for at least about 100 microseconds.

7. (Previously Presented) The substrate of claim 1 wherein the embedded programmable memory devices will pass from about 10 to about 200 microamps of current at about 2 volts in a programmed state.

8. (Previously Presented) The substrate of claim 1 wherein the embedded programmable memory devices will pass less than 3 microamps of current at about 2 volts in an unprogrammed state.

9. (Cancelled)

10. (Currently Amended) A printhead for an ink jet printer containing the semiconductor substrate of ~~claim 9~~ claim 1.

11. (Currently Amended) The printhead of claim 10 wherein the layer comprises a material selected from the group consisting of a photoresist material[,] and a metal ~~layer, said layer having ultraviolet light blocking properties.~~

12. (Currently Amended) The printhead of claim 10 wherein the layer comprises a polyimide nozzle plate.

13. (Currently Amended) An ink jet printer cartridge for an ink jet printer comprising:  
a cartridge body having an ink supply source; and  
a printhead attached to the cartridge body in fluid communication with the ink supply source,  
the printhead comprising:  
a substrate having a plurality of ink ejection devices;  
a plurality of driver devices for driving the plurality of ink ejection devices;  
a nonvolatile programmable memory matrix containing embedded programmable  
memory devices, the matrix being operatively connected to the ink jet printer  
for storing information for operation of the printer wherein the memory matrix  
is erasable by ultraviolet light;

a photoresist layer disposed adjacent the programmable memory matrix, said photoresist layer having properties sufficient to block ultraviolet light having a wavelength below about 400 nanometers; and

a nozzle plate attached to the substrate for ejecting ink therefrom upon activation of the ink ejection devices.

14. (Original) The ink jet printer cartridge of claim 13 wherein the embedded programmable memory devices comprise transistors selected from the group consisting of PMOS and NMOS floating gate transistors.

15. (Original) The ink jet printer cartridge of claim 13 wherein the embedded programmable memory devices have a memory density of greater than about 200 bits per square millimeter.

16. (Original) The ink jet printer cartridge of claim 13 wherein the programmable memory matrix comprises floating gate transistors.

17. (Original) The ink jet printer cartridge of claim 13 wherein the programmable memory matrix comprises more than 128 memory devices.

18. (Original) The ink jet printer cartridge of claim 13 wherein the embedded programmable memory devices are programmable by applying a voltage of greater than about 8 volts for at least about 100 microseconds.

19. (Original) The ink jet printer cartridge of claim 13 wherein the embedded programmable memory devices will pass from about 10 to about 200 microamps of current at about 2 volts in a programmed state.

20. (Original) The ink jet printer cartridge of claim 13 wherein the embedded programmable memory devices will pass less than 3 microamps of current at about 2 volts in an unprogrammed state.

21. (Cancelled)

22. (Currently Amended) The ink jet printer cartridge of claim 13 wherein ~~the memory matrix is erasable by ultraviolet light and~~ the nozzle plate comprises a polyimide nozzle plate having properties sufficient to block ultraviolet light having a wavelength below about 400 nanometers.

23. (Currently Amended) ~~A printhead for a~~ A micro-fluid ejecting device; ~~the printhead~~ comprising:

a micro-fluid ejecting head having:

a plurality of fluid ejection devices;

a plurality of driver devices for driving the plurality of fluid ejection devices; and

a nonvolatile programmable memory matrix containing embedded programmable memory devices, the matrix being capable of being operatively connected to a micro-fluid ejecting device for storing information for operation of the micro-fluid ejecting device[.]; and

a controller external of the micro-fluid ejecting head and in communication with the nonvolatile programmable memory matrix.

24. (Currently Amended) The ~~printhead~~ micro-fluid ejecting device of claim 23, ~~further comprising a controller~~ wherein at least a portion of the matrix is directly readable by the controller.

25. (Cancelled)

26. (Currently Amended) The ~~printhead~~ micro-fluid ejecting device of claim 23, wherein the programmable memory devices are embedded in a semiconductor.

27. (Currently Amended) The ~~printhead~~ micro-fluid ejecting device of claim 26, wherein the semiconductor comprises silicon.

28. (Currently Amended) The ~~printhead~~ micro-fluid ejecting device of claim 23, wherein the driver devices comprise transistors.